In the Claims

Claims 1-30 (Canceled).

31. (Previously presented) An engagement probe comprising:

a substrate comprising bulk semiconductive material;

a projection supported over the substrate and comprising material of the substrate; and

a grouping of a plurality of projecting apexes extending from the projection.

32. (Previously presented) The engagement probe of claim 31 comprising a plurality of such groupings for engaging multiple conductive pads.

33. (Previously Presented) The engagement probe of claim 31 wherein the apexes are in the shape of multiple knife-edge lines.

34. (Previously Presented) The engagement probe of claim 31 wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least one polygon.

35. (Previously Presented) The engagement probe of claim 31 wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least two polygons one of which is received entirely within the other.

36. (Previously Presented) The engagement probe of claim 31 wherein the grouping of apexes is formed on the projection which is supported by another projection, the another projection extending directly from the substrate.

37. (Previously Presented) The engagement probe of claim 31 wherein the apexes have a selected projecting distance, the projecting distance being about one-half the thickness of the conductive pad which the apparatus is adapted to engage.

38. (Previously Presented) The engagement probe of claim 31 wherein the apexes project from a common plane of the projection, the apexes having respective tips and bases, the bases of adjacent projecting apexes being spaced from one another to define a penetration stop plane therebetween.

39. (Previously Presented) The engagement probe of claim 31 wherein the apexes project from a common plane of the projection, the apexes having respective tips and bases, the bases of adjacent projecting apexes being spaced from one another to define a penetration stop plane therebetween, the tips being a distance from the penetration stop plane of about one-half the thickness of the conductive pad which the apparatus is adapted to engage.

40. (Previously Presented) The engagement probe of claim 31 wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines interconnecting to form at least one fully enclosed polygon.

41. (Previously Presented) The engagement probe of claim 31 wherein outermost portions of the electrically conductive apexes constitute a first electrically conductive material, and wherein the conductive pads for which the probe is adapted have outermost portions constituting a second electrically conductive material; the first and second electrically conductive materials being different.

42. (Previously Presented) An engagement probe formed from a semiconductor material and having a grouping of a plurality of projecting apexes positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least one polygon.

43. (Previously Presented) An engagement probe formed from a semiconductor material and having a grouping of a plurality of projecting apexes positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least two polygons one of which is received entirely within the other.

44. (Previously Presented) An engagement probe formed from a semiconductor material and having a grouping of a plurality of projecting apexes positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines interconnecting to form at least one fully enclosed polygon.

45. (Previously Presented) The engagement probe of claim 31 wherein the plurality of the projecting apexes extend from a substantially planar uppermost surface of the projection.

46. (Previously Presented) The engagement probe of claim 31 wherein an entirety of the projection is spaced from the substrate.

Claim 47-48 (Canceled).

49. (Previously Presented) An engagement probe comprising:

a substrate;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least two polygons one of which is received entirely within the other.

50. (Previously presented) An engagement probe comprising:

a substrate;

a projection supported over a side of the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the grouping of apexes is formed on the projection which is supported by another projection, the another projection extending directly from the side of the substrate.

51. (Previously presented) An engagement probe comprising:

a substrate comprising monocrystalline silicon;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes project from a common plane of the projection, the apexes having respective tips and bases, the bases of adjacent projecting apexes being spaced from one another to define a penetration stop plane therebetween.

52. (Previously presented) An engagement probe comprising:

a substrate;

a first projection supported over the substrate and comprising material of the substrate;

a second projection over the first projection and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the second projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes project from a common plane of the second projection, the apexes having respective tips and bases, the bases of adjacent projecting apexes being spaced from one another to define a penetration stop plane therebetween, the tips being a distance from the penetration stop plane of about one-half the thickness of the conductive pad which the apparatus is adapted to engage.

53. (Currently amended) An engagement probe comprising:

a substrate;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein an entirety of the projection is spaced from the substrate and has a different shape relative the projecting apexes other than size dimensions.

54. (Previously Presented) An engagement probe comprising:

a substrate;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the substrate comprises bulk silicon.

55. (Previously Presented) The engagement probe of claim 31 further comprising an intermediate structure between the projection and the substrate, wherein the intermediate structure comprises a lateral dimension that is different from a lateral dimension of the substrate and a lateral dimension of the projection.

56. (Previously Presented) The engagement probe of claim 53 further comprising an intermediate structure between the projection and the substrate, the intermediate structure providing the spacing of the projection from the substrate, and wherein the intermediate structure comprises a lateral dimension that is different from a lateral dimension of the substrate and a lateral dimension of the projection.

57. (Previously Presented) The engagement probe of claim 56 wherein the lateral dimensions of the substrate and the projection are different.

58. (Previously presented) The engagement probe of claim 53 wherein the projecting apexes comprise bulk silicon.

59. (Previously Presented) The engagement probe of claim 54 further comprising an intermediate structure between the projection and the substrate, wherein the intermediate structure comprises a lateral dimension that is different from a lateral dimension of the substrate and a lateral dimension of the projection.

60. (Previously presented) The engagement probe of claim 31 wherein the projection comprises a lateral dimension less than a lateral dimension of the substrate.

61. (Previously presented) The engagement probe of claim 31 wherein the substrate comprises a wafer.

62. (Previously presented) The engagement probe of claim 31 wherein the bulk semiconductive material comprises bulk silicon.

63. (Previously presented) An engagement probe comprising:

a substrate;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate;

wherein the projection comprises a lateral dimension less than a lateral dimension of the substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least one polygon.

64. (Previously presented) The engagement probe of claim 63 wherein the apexes are positioned to form at least two polygons one of which is received entirely within the other.

65. (Previously presented) The engagement probe of claim 63 wherein the apexes are positioned to form the multiple knife-edge lines interconnecting to form at least one fully enclosed polygon.

66. (New) The engagement probe of claim 31 wherein the material of the projection is the bulk semiconductive material.

67. (New) The engagement probe of claim 66 wherein the material of the plurality of the projecting apexes is the bulk semiconductive material.

68. (New) The engagement probe of claim 66 wherein the bulk semiconductive material is material of a wafer.

69. (New) The engagement probe of claim 51 wherein the material of the projection is the bulk semiconductive material.

70. (New) The engagement probe of claim 69 wherein the material of the plurality of the projecting apexes is the bulk semiconductive material.

71. (New) The engagement probe of claim 69 wherein the bulk semiconductive material is material of a wafer.

72. (New) The engagement probe of claim 54 wherein the material of the projection is the bulk semiconductive material.

73. (New) The engagement probe of claim 72 wherein the material of the plurality of the projecting apexes is the bulk semiconductive material.

74. (New) The engagement probe of claim 72 wherein the bulk semiconductive material is material of a wafer.